

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

Claims 1-7 (canceled)

Claim 8. (Currently amended) A method for making a field effect transistor with a current channel with longitudinal stress, comprising the steps of:

- a) selectively forming an undercut area under a middle portion of the channel in ~~selected regions of the perimeter of said channel~~; and
- b) forming a compressive film in the undercut area so that longitudinal stress is created in the channel.

Claims 9-10. (Canceled)

Claim 11. (Currently amended) The method of claim 8 ~~10~~ wherein the channel is released in the middle portion.

Claim 12. (Original) The method of claim 8 wherein the undercut area is created by etching a buried oxide layer from under the channel.

Claim 13. (Original) The method of claim 8 wherein the compressive film is formed by depositing polysilicon and then oxidizing the polysilicon.

Claims 14-16. (Canceled)